

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 118008		APPLICATION NO. New U.S. Patent Application  10/728,746	
INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)				APPLICANT Kanji NATORI			
				FILING DATE December 8, 2003		ART UNIT 2818	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
JM	1	US 6,248,633 B1	6/19/2001	OGURA et al.	438	267	
JM	2	US 6,177,318 B1	1/23/2001	OGURA et al.	438	267	
JM	3	5,494,838	2/27/1996	CHANG et al.	438	264	
JM	4	5,422,504	6/6/1995	CHANG et al.	365	185.15	
JM	5	5,969,383	10/19/1999	CHANG et al.	257	316	
JM	6	5,408,115	4/18/1995	CHANG	253	324	
JM	7	US 6,255,166 B1	7/3/2001	OGURA et al.	438	257	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
JM	8	JP A 2001-156188 w/ Abst & Trans	6/8/2001	Japan			
JM	9	JP A 07-161851 w/ Abst & Trans	6/23/1995	Japan			
JM	10	JP A 06-181319 w/ Abst & Trans	6/28/1994	Japan			
JM	11	JP A 11-074389 w/ Abst & Trans	3/16/1999	Japan			
JM	12	JP A 2002-313090 w/ Abst & Trans	10/25/2002	Japan			
JM	13	JP B1 2978477 w/ Translation	9/10/1999	Japan			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
JM	14	Yutaka HAYASHI et al., "Twin MONOS Cell with Dual Control Gates", 2000 Symposium on VLSI Technology Digest of Technical Papers.					
		X					
JM	15	Kuo-Tung CHANG et al., "A New SONOS Memory using Source-Side Injection for Programming", IEEE Electron Device Letters, Vol. 19, No. 7, July 1998, Pgs. 253-255.					
		X					
	16	Wei-Ming Chen et al., "A Novel Flash Memory Device with Split Gate Source Side Injection and ONO Charge Storage Stack (SPIN)", 1997 Symposium on VLSI Technology Digest of Technical Papers, Pgs. 63-64.					
		X					
EXAMINER					DATE CONSIDERED		
SON MAI					12/21/04		
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Date: December 8, 2003